

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		DOCKET NO. 8229-014-27		SERIAL NO. 09/975,256	
LIST OF REFERENCES CITED BY APPLICANT (Use Several Sheets if Necessary)				APPLICANT Krishnaswamy RAMKUMAR, et al.			
				FILING DATE October 12, 2001		GROUP ART UNIT 2812	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Det</i>	AA	5,403,786	8/4/95	Hori	/	/	
<i>↓</i>	AB	5,521,127	5/28/96	Hori	/	/	
<i>↓</i>	AC	5,629,221	5/13/97	Chao, et al.	/	/	
<i>Det</i>	AD	5,880,040	3/9/99	Sun, et al.	/	/	
	AE						
	AF						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AG						
	AH						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>Det</i>	AI	Gusev, et al., "Growth and Characterization of Ultrathin Nitrided Silicon Oxide Films", IBM J. Res. Develop., 43, 3, 265-286 (1999).					
<i>↓</i>	AJ	Hook, et al., "Nitrided Gate Oxides for 3.3-V Logic Application: Reliability and Device Design Considerations", IBM J. Res. Develop., 43, 3, 393-406 (1999).					
<i>↓</i>	AK	Buchanan, "Scaling the Gate Dielectric: Materials Integration, and Reliability", IBM J. Res. Develop., 43, 3, 245-264 (1999).					
<i>Det</i>	AL	Evans, et al., "High Performance CMOS Devices with 20 Å Engineered Oxynitrided Gate Dielectrics", paper presented at Semicon Korea Technical Symposium (2000).					
	AM						
	AN						

EXAMINER

DATE CONSIDERED 1-13-03

*EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.